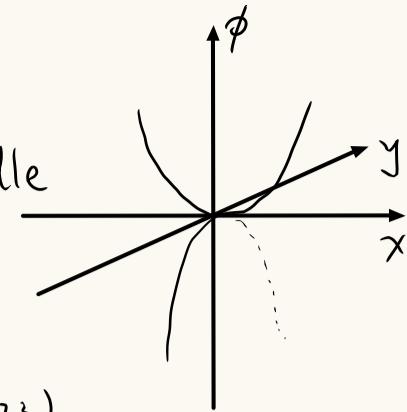


# 1. Paul trap / Radio-frequency trap

time-varying potential  $\phi = \frac{V_0}{2r_0^2} \underbrace{\cos(\omega_{rf}t)}_{\text{dynamical trapping}} (x^2 - y^2) \sim \text{saddle}$



Generally in 3D,  $\phi = \underbrace{\frac{V_0}{2r_0^2} (\alpha x^2 + \beta y^2 + \gamma z^2)}_{dc} + \underbrace{\frac{V_{rf}}{2r_0^2} \cos(\omega_{rf}t) (\alpha' x^2 + \beta' y^2 + \gamma' z^2)}_{rf}$

$$\text{Laplace's equation} \Rightarrow \begin{cases} \alpha + \beta + \gamma = 0 \\ \alpha' + \beta' + \gamma' = 0 \end{cases}$$

Choose  $\alpha = \beta = \gamma = 0$ , and to choose a cylindrically symmetric trap, we need  $\alpha' = \beta' = -\gamma' = 1$

$$\Rightarrow \phi = \frac{V_{rf}}{2r_0^2} \cos(\omega_{rf}t) (x^2 + y^2 - z^2) = \frac{V_{rf}}{2r_0^2} \cos(\omega_{rf}t) (r^2 - z^2)$$

Cartesian Coordinate      Cylindrical Coordinate

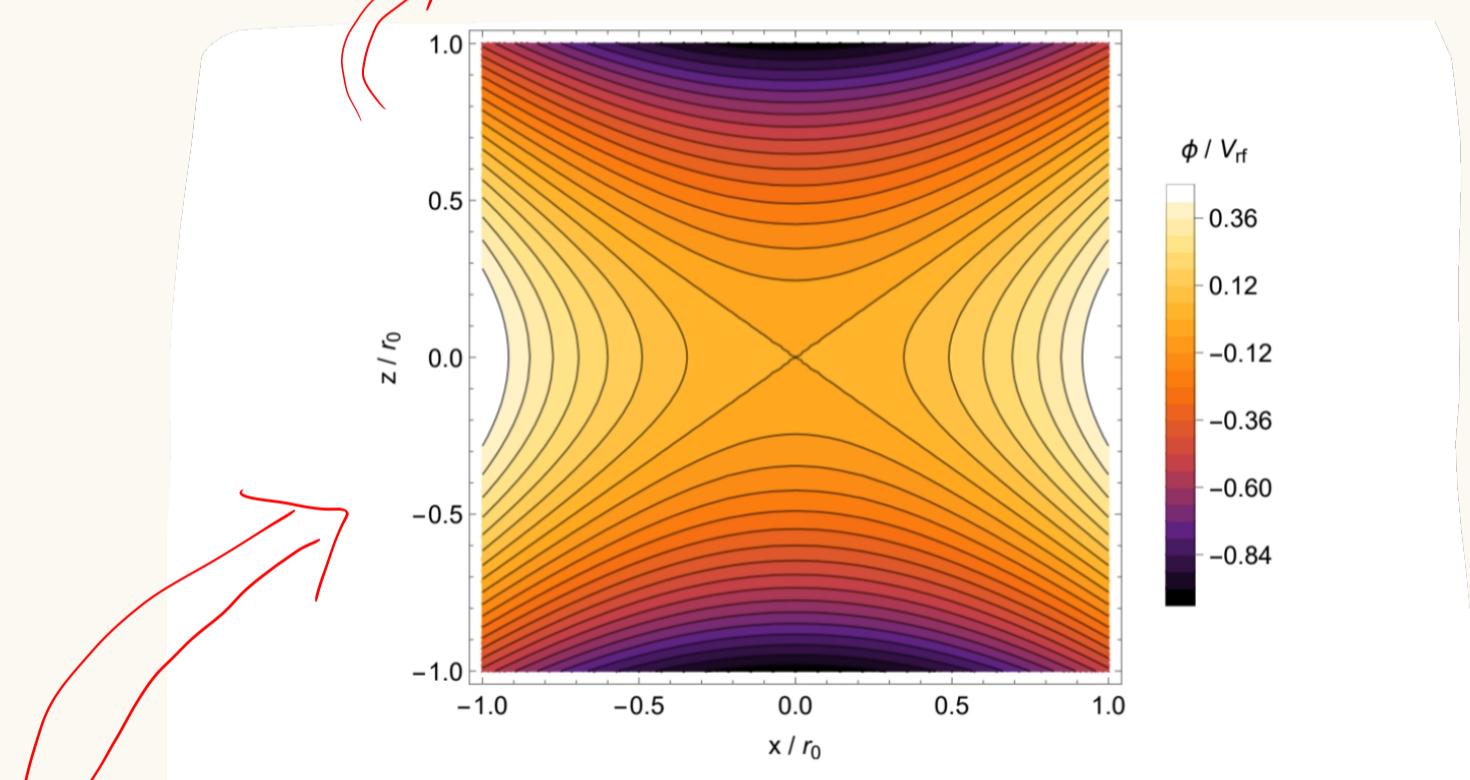


Figure 6.1: Electrostatic potential in the  $xz$ -plane for a 3D rf ion trap. The potential has cylindrical symmetry about the  $z$ -axis. The values of the contours correspond to Eq. (6.4) at  $t = 0$ .

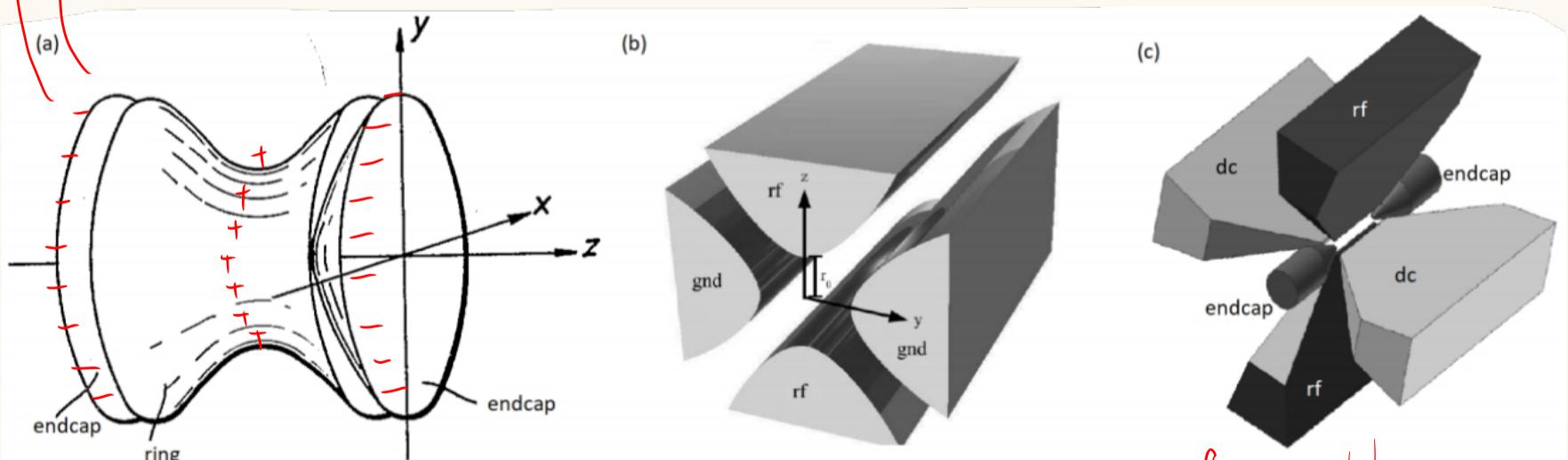


Figure 6.2: Electrode geometries for making rf traps. (a) Cylindrically symmetric 3D rf trap. (b) Linear rf trap with no confinement along the long direction. (c) Linear rf trap with endcap electrodes for static confinement along the long direction.

↓  
used for trapping linear strings of ions

Consider an ion of charge  $e$  and mass  $m$  in a potential of the general form.  
Consider the  $x$ -direction and set  $\alpha = \alpha' = 1$ , the equation of motion:

$$T = \frac{w_{rf} t}{2}, \quad \alpha_x = \frac{4eV_0}{mr_0^2 w_{rf}^2}, \quad q_x = -\frac{2eV_{rf}}{mr_0^2 w_{rf}^2} \quad \frac{d^2x}{dt^2} = -\frac{e}{mr_0^2} [V_0 + V_{rf} \cos(\omega_{rf} t)] x$$

$$\frac{d^2x}{d\tau^2} + [\alpha_x - 2q_x \cos(2\tau)] x = 0 \quad \text{Mathieu equation}$$

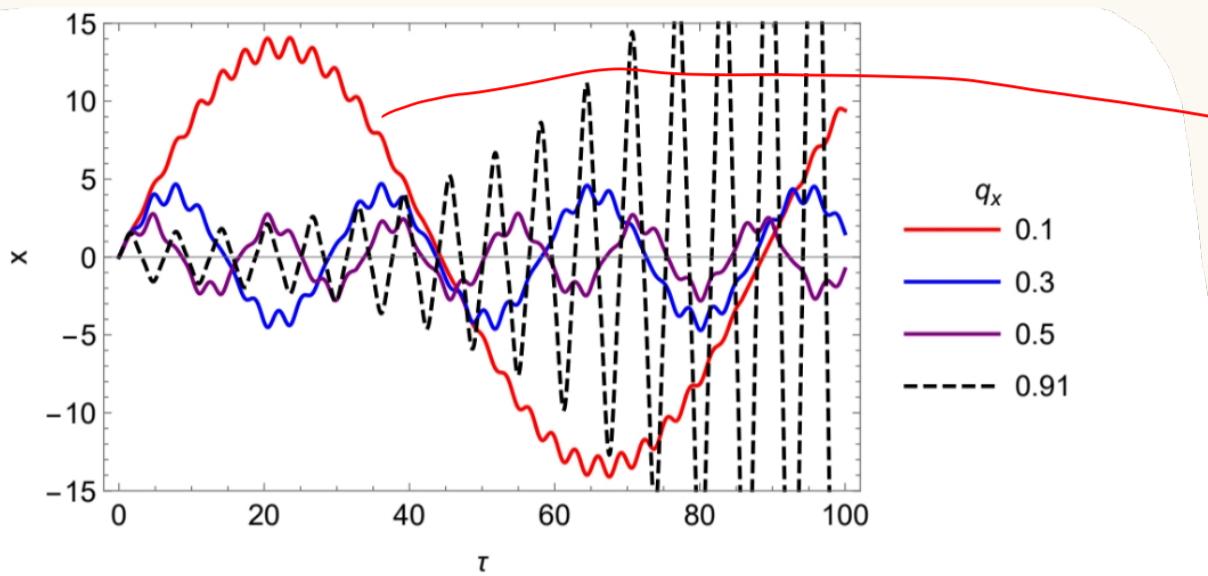


Figure 6.3: Solutions to the Mathieu equation, with  $\alpha_x = 0$  and various values of  $q_x$ . The motion becomes unstable for  $q_x > 0.9$  (black dashed line).

no dc potential

micromotion: a small amplitude oscillation at the rf frequency  
superimpose  
secular motion: a slower and larger amplitude oscillation

$q_x \rightarrow$ , the frequencies of the two oscillations approach one another

The behavior at small  $q_x$  suggests  $x = x_f + x_s$  (fast and slow oscillation), we assume  $x_f \ll x_s$ ,  $dx_f/dt \gg dx_s/dt$

$$\implies \frac{d^2x_f}{d\tau^2} = 2q_x \cos(2\tau) x_s$$

Takes  $x_s$  to be a constant over the short period of high-frequency oscillation, so that

$$x_f = -\frac{q_x x_s}{2} \cos(2\tau)$$

$$\implies \frac{d^2(x_s + x_f)}{d\tau^2} = 2q_x \cos(2\tau) (x_s + x_f)$$

$$\frac{d^2x_s}{d\tau^2} + \frac{d^2x_f}{d\tau^2} = 2q_x x_s \underbrace{\cos(2\tau)}_{0} - q_x^2 x_s \underbrace{\cos^2(2\tau)}_{\frac{1}{2}}$$

time average over one period of the rf drive

$$\implies \frac{d^2x_s}{d\tau^2} = -\frac{q_x^2}{2} x_s$$

$$\implies \frac{d^2x_s}{dt^2} = -\left(\frac{e^2 V_{rf}^2}{2m^2 r_0^4 w_{rf}^2}\right) x_s$$

slow motion is that of a harmonic oscillator of angular frequency  $\omega_x = \frac{eV_{rf}}{\sqrt{2m^2 r_0^4 w_{rf}^2}}$   
 $\omega_z = 2\omega_x = 2\omega_y$  for a cylindrical trap

macroscopic ion traps  $\sim$  trap frequencies  $\sim 1\text{MHz}$

microscopic ion traps formed on chips  $\sim$  trap frequencies  $\sim 10-100\text{MHz}$

## 2. Penning trap

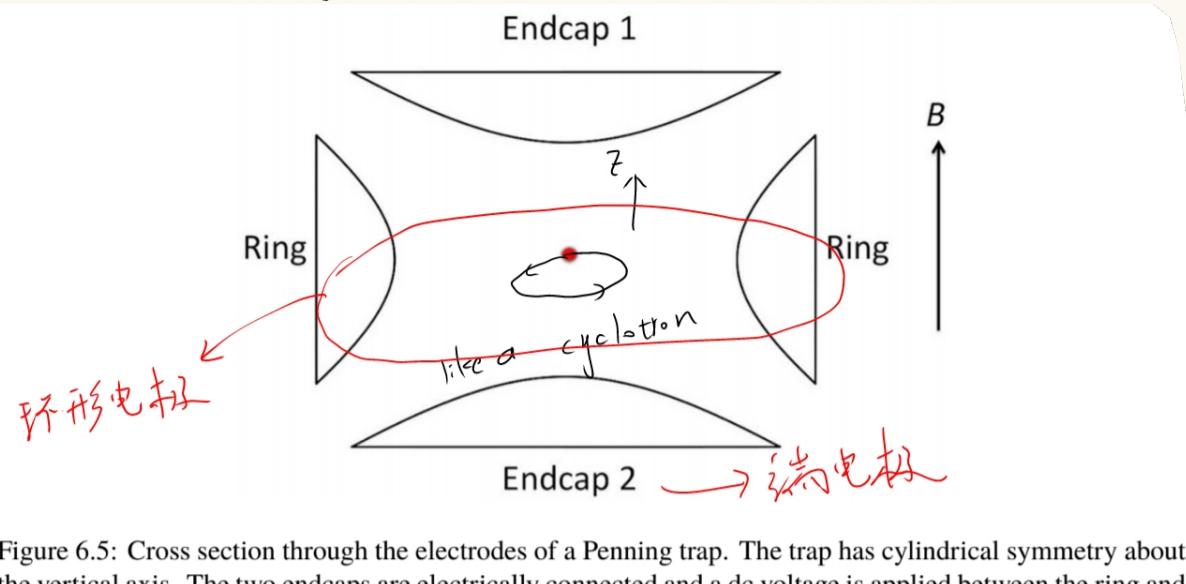
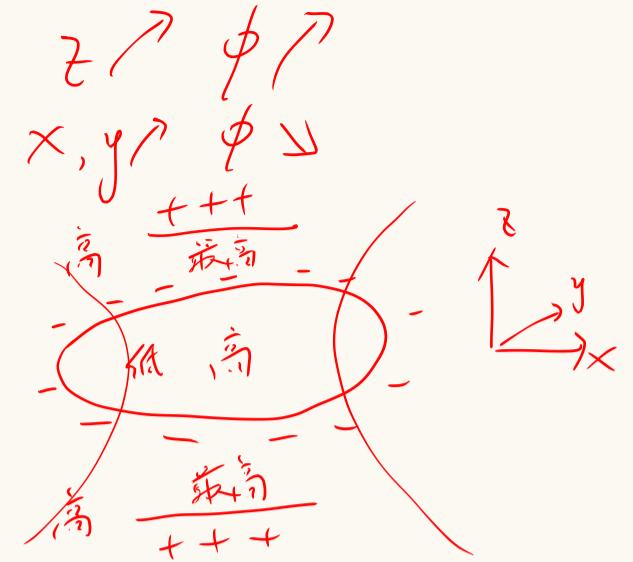


Figure 6.5: Cross section through the electrodes of a Penning trap. The trap has cylindrical symmetry about the vertical axis. The two endcaps are electrically connected and a dc voltage is applied between the ring and the endcaps.



$$\phi = \frac{V_0}{2r_0^2} (z^2 - \frac{1}{2}(x^2 + y^2))$$

$$\begin{cases} \vec{E} = -\nabla \phi = -\frac{V_0}{r_0^2} (\vec{z} - \frac{1}{2}(\vec{x} + \vec{y})) \\ \vec{B} = B \vec{z} \\ \vec{F} = e(\vec{E} + v \times \vec{B}) \end{cases}$$

$\Rightarrow$

$$\begin{cases} \dot{x} = \frac{1}{2} w_z^2 x + w_c y \\ \dot{y} = \frac{1}{2} w_z^2 y - w_c x \\ \dot{z} = -w_z^2 z \end{cases}$$

cyclotron frequency  $w_c = \frac{eB}{m}$

$$\begin{cases} u = x + iy \\ \dot{u} = \frac{1}{2} w_z^2 u - iw_c u \end{cases}$$

axial frequency  $w_z = \sqrt{\frac{eV_0}{mr_0^2}}$

$$\downarrow$$

$$\dot{u} = \frac{1}{2} w_z^2 u - iw_c u$$

solution of the form  $u = A e^{-i\omega t}$

$$w^2 - w_c w + \frac{1}{2} w_z^2 = 0$$

$$\begin{cases} w_+ = \frac{1}{2} (w_c + \sqrt{w_c^2 + 2w_z^2}) \\ w_- = \frac{1}{2} (w_c - \sqrt{w_c^2 + 2w_z^2}) \end{cases}$$

modified cyclotron frequency  
magnetron frequency  $w_m$

$$w_+ \gg w_z \gg w_-$$

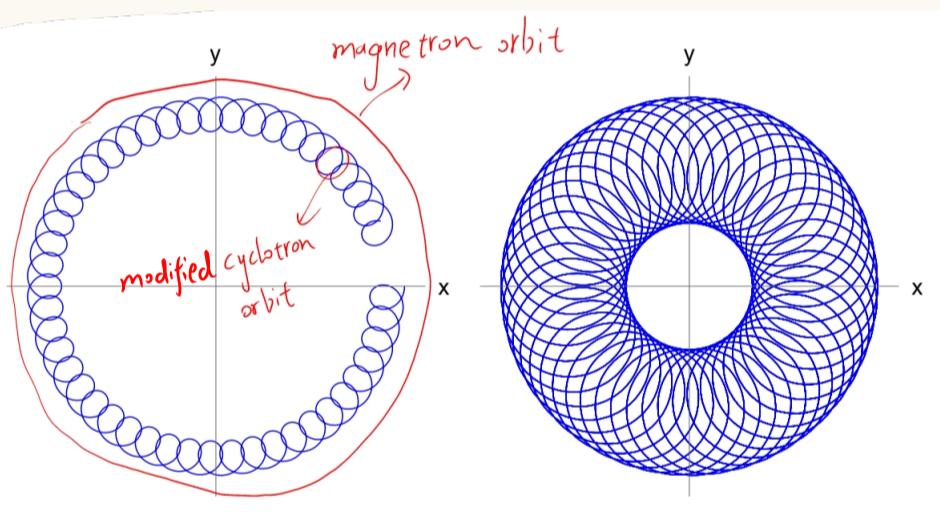


Figure 6.6: Example trajectories in the radial plane of an ion in a Penning trap. Small circles are cyclotron orbits, and the larger one is the magnetron orbit.

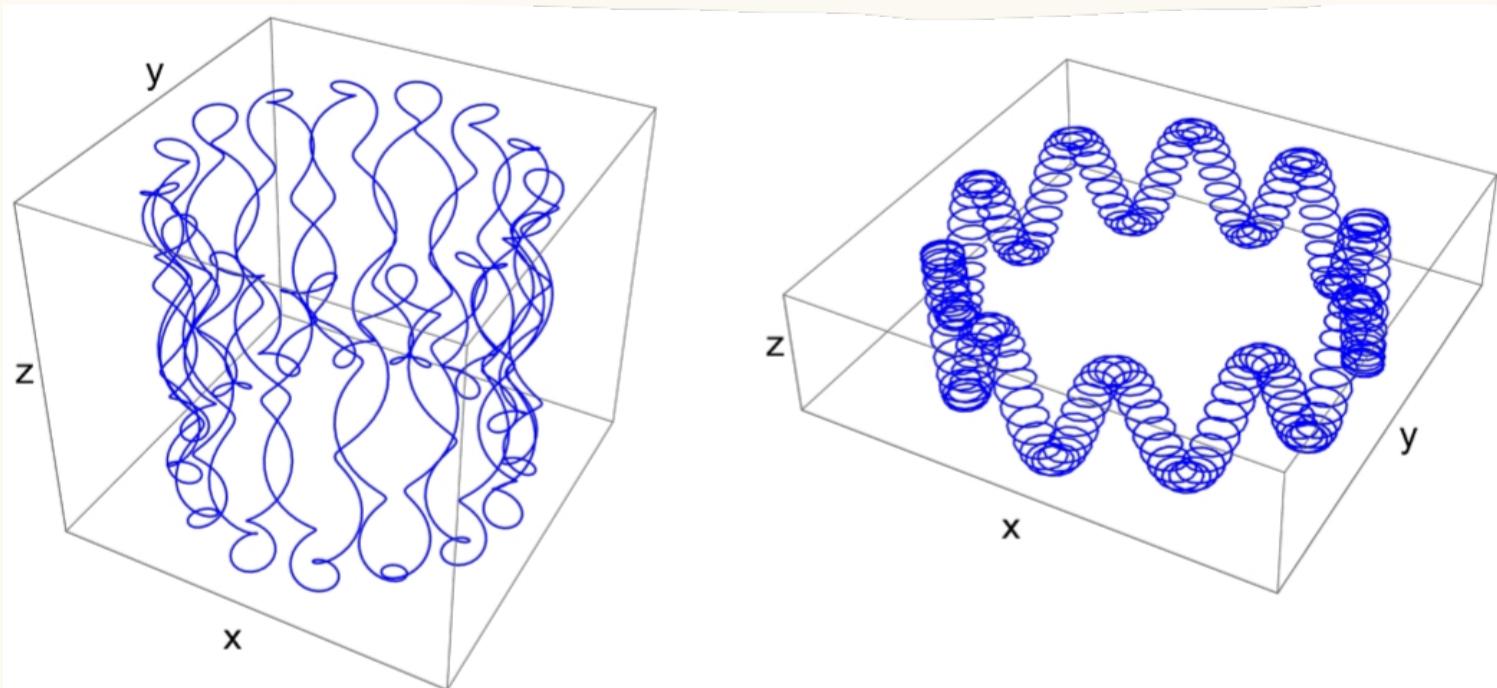


Figure 6.7: Examples of three-dimensional trajectories of an ion in a Penning trap.

### 3. Sideband cooling



We want to find a different choice of qubit gives zero sensitivity to magnetic field at a particular non-zero field, i.e.  $df/dB = 0$

Clock states

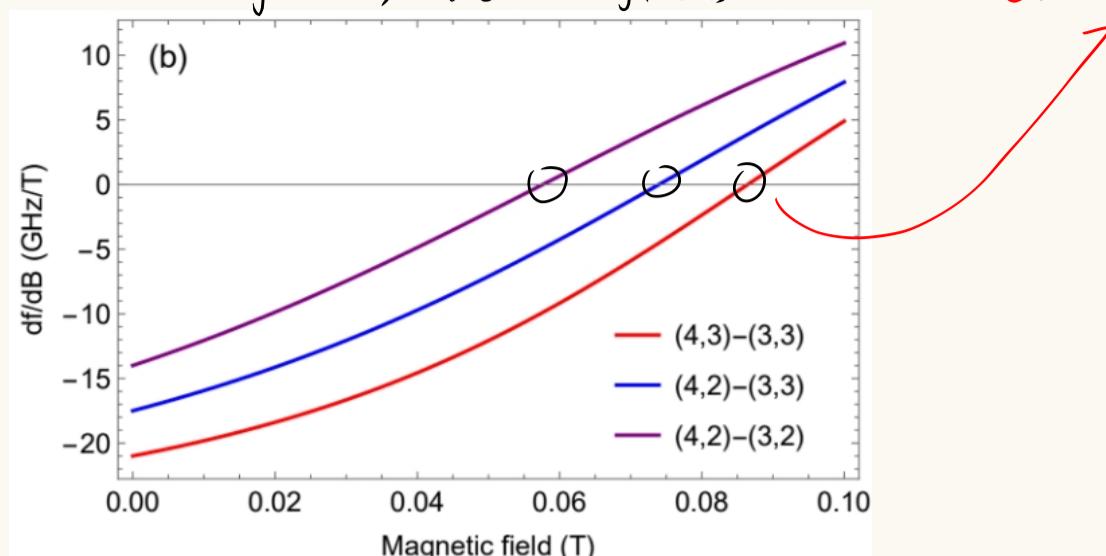
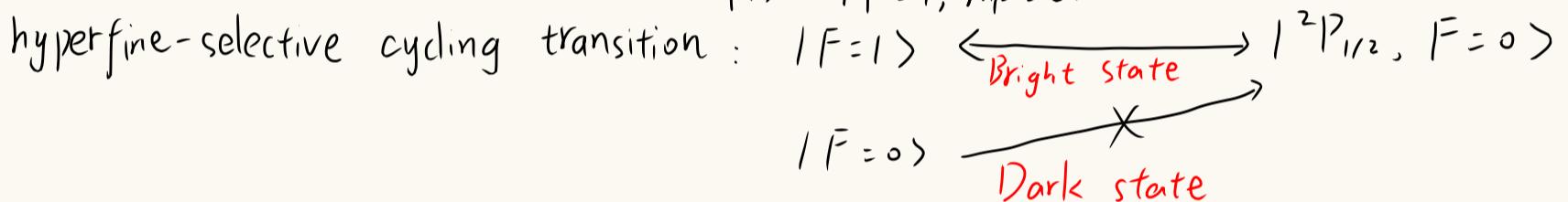


Figure 6.15: (a) Zeeman splitting of the ground state hyperfine components of  $^{43}\text{Ca}^+$ . (b) Sensitivity of qubit frequency to magnetic field,  $df/dB$ , as a function of magnetic field, for a few different qubit choices.

Readout: based on a hyperfine-selective cycling transition.

e.g. For  $^{171}\text{Yb}^+$   $^2S_{1/2} \Rightarrow |0\rangle = |F=0, m_F=0\rangle$   
 $|1\rangle = |F=1, m_F=0\rangle$



Here,  $|0\rangle = |^2S_{1/2}, F=4\rangle \xrightarrow{\text{shelving}} |^2D_{5/2}$   
 $|1\rangle = |^2S_{1/2}, F=3\rangle$

cycling transition:  $^2S_{1/2} \xleftrightarrow{397\text{nm}} ^2P_{1/2}$   
 Bright state :  $|1\rangle$

Dark state :  $|0\rangle$  (Because of shelving )

Once the ion reaches  $^2D_{5/2}$ , it remains there for a long time, because the state has such a long lifetime.

This is called "shelving"

### ③ Single-qubit gates

The dynamics here are simply that of a two-level atom interacting with light. The light is resonant with the transition ( $\delta = 0$ )

$$\text{light: } \vec{E} = \vec{E}_0 \cos(\omega t + \phi)$$

$$\begin{cases} i \frac{dc_1}{dt} = \frac{\Omega}{2} e^{i\phi} c_2 \\ i \frac{dc_2}{dt} = \frac{\Omega}{2} e^{-i\phi} c_1 \end{cases} \Rightarrow \begin{cases} c_1(t) = \cos(\Omega t/2) c_1(0) - i e^{i\phi} \sin(\Omega t/2) c_2(0) \\ c_2(t) = -i e^{-i\phi} \sin(\Omega t/2) c_1(0) + \cos(\Omega t/2) c_2(0) \end{cases}$$

$$c_1(t)|1\rangle + c_2(t)|2\rangle = \begin{pmatrix} c_1(t) \\ c_2(t) \end{pmatrix} = U(t) \begin{pmatrix} c_1(0) \\ c_2(0) \end{pmatrix}, \quad U(t) = \begin{pmatrix} \cos(\Omega t/2) & -i e^{i\phi} \sin(\Omega t/2) \\ -i e^{-i\phi} \sin(\Omega t/2) & \cos(\Omega t/2) \end{pmatrix}$$

When  $\phi = 0 \quad \Omega t = \pi/2 \quad (\frac{\pi}{2} \text{ pulse})$

$$c_1(t) = \frac{1}{\sqrt{2}} (c_1(0) - i c_2(0)) \sim |1\rangle \rightarrow \frac{1}{\sqrt{2}} (|1\rangle - i|2\rangle)$$

$$c_2(t) = \frac{1}{\sqrt{2}} (-i c_1(0) + c_2(0)) \sim |2\rangle \rightarrow \frac{1}{\sqrt{2}} (-i|1\rangle + |2\rangle)$$

$\Omega t = \pi \quad (\pi \text{ pulse})$

$$|1\rangle \rightarrow -i|2\rangle$$

$$|2\rangle \rightarrow -i|1\rangle$$

$\Omega t = 2\pi \quad (2\pi \text{ pulse})$

$$|1\rangle \rightarrow -|1\rangle$$

$$|2\rangle \rightarrow -|2\rangle$$

For an optical qubit, the transitions are driven using laser pulses.

For a hyperfine qubit (two states have the same parity):

single qubit manipulations { be driven directly in the microwave domain

long wavelength (a magnetic dipole transition)

difficult to address the individual ions ??

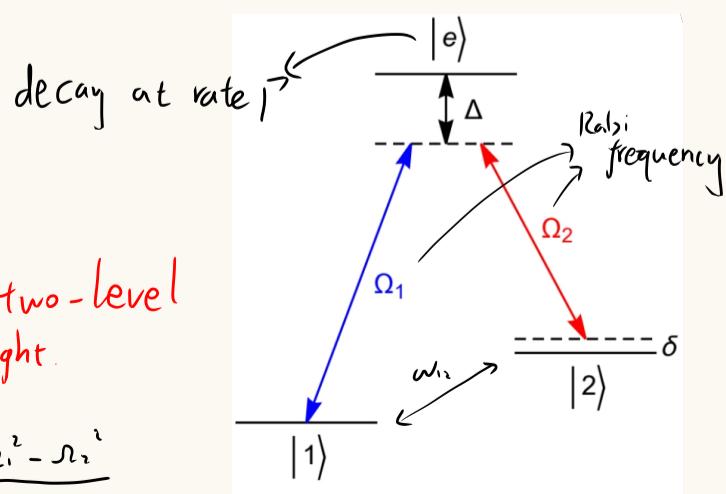
Using small microwave transmission lines microfabricated into the chip

using a Raman transition in the optical domain (a two-photon process)

two lasers:  $\omega_1, \omega_2$

$$\Delta = \omega_1 - \omega_2 - \omega_{12}$$

$$\Delta \gg \Omega_1, \Omega_2, \Gamma$$



The dynamics are identical to that of a two-level system driven by a single frequency of light.

$$\text{effective Rabi frequency } \Omega_{\text{eff}} = \frac{\Omega_1 \Omega_2}{2\Delta}$$

$$\text{effective two-photon detuning } \delta_{\text{eff}} = \Delta - \frac{\Omega_1^2 + \Omega_2^2}{4\Delta}$$

Figure 6.16: Driving a Raman transition

(4) Two-qubit gates (fidelities 99.9%, gate speeds 100 μs)

single ion axial trapping frequency

normal modes of motion in the axial direction } Centre of Mass (COM) at  $\omega_z$  oscillate in the same phase and with the same amplitude

a stretch or breathing motion at  $\sqrt{3}\omega_z$  (for two-ion chain) oscillate in opposite directions, the ions closer to centre move less than those near the edges

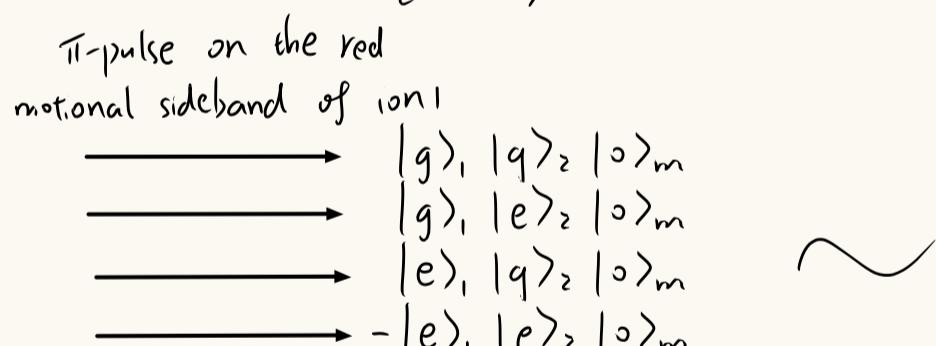
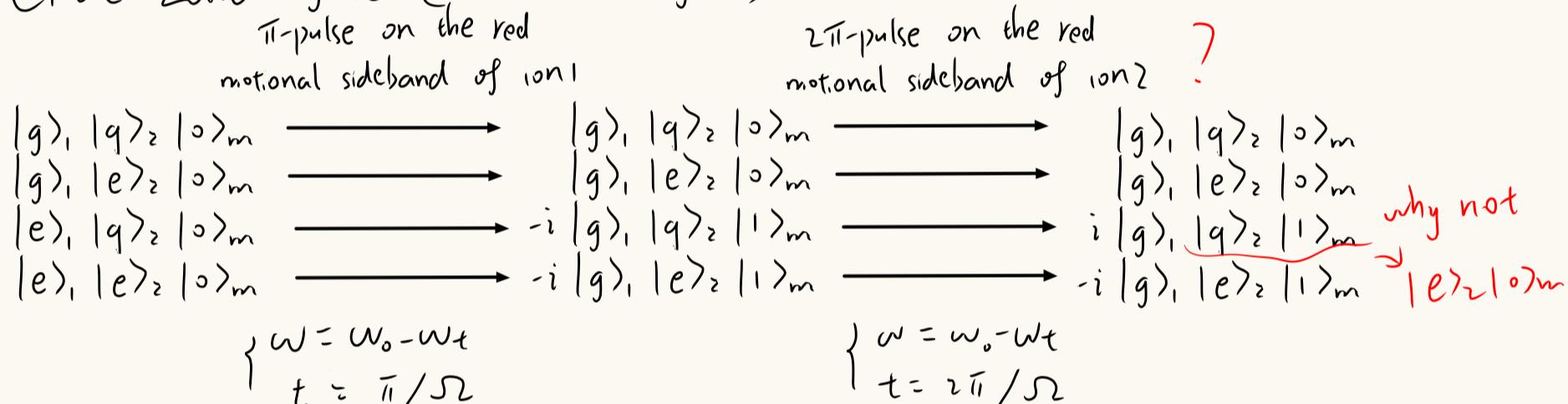
Choose the breathing mode, assume in the motional ground state

ions: 1, 2

internal states { qubit states  $|g\rangle, |e\rangle$   
auxiliary state  $|a\rangle$

motional state:  $|0\rangle$

### Cirac-Zoller gate (Controlled-Z gate)



Drawbacks { ① requires ions to be cooled to the ground state of their collective motion  
 ② requires individual addressing of each ion

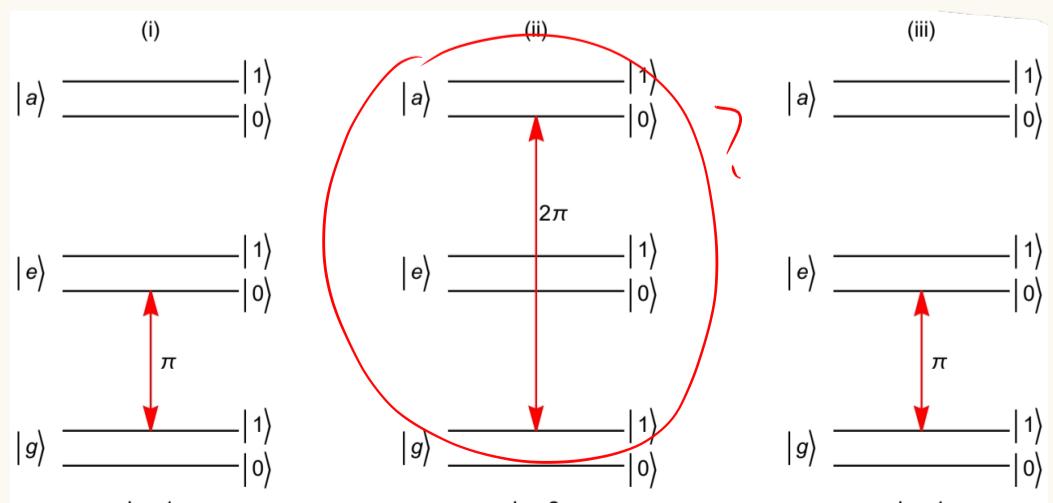


Figure 6.17: Implementation of a controlled-Z gate between a pair of ion qubits.  $|g\rangle$  and  $|e\rangle$  are the qubit states, and  $|a\rangle$  is an auxiliary state.  $|0\rangle$  and  $|1\rangle$  refer to the (shared) motional state. The steps are applied in sequence. (i) The state of qubit 1 is mapped to the motional state. (ii) A  $\pi$  phase shift is applied to the motional state conditional on the state of qubit 2. (iii) The motional state is mapped back to ion 1.

